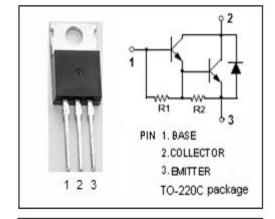


# isc Silicon NPN Darlington Power Transistor

## **BD645**

#### **DESCRIPTION**

- Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 60V(Min)
- · High DC Current Gain
  - : h<sub>FE</sub>= 750(Min) @I<sub>C</sub>= 3A
- Low Saturation Voltage
- Complement to Type BD646
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



### **APPLICATIONS**

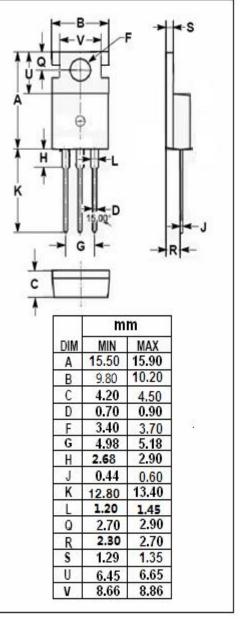
 Designed for use as complementary AF push-pull output stage applications

#### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	80	V	
VCEO	Collector-Emitter Voltage	60	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
Ic	Collector Current-Continuous	8	Α	
Іср	Collector Current-Peak	12	Α	
I <sub>B</sub>	Base Current-Continuous	0.15	Α	
Pc	Collector Power Dissipation @ T <sub>a</sub> =25°C	2	10/	
	Collector Power Dissipation @ T <sub>C</sub> =25°C	62.5	W	
TJ	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-65~150	$^{\circ}$	

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	2	°C/W
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient	70	°C/W





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**BD645** 

#### **ELECTRICAL CHARACTERISTICS**

 $T_{\text{C}}$ =25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> = 0	60			V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	Ic= 3A; I <sub>в</sub> = 12mA			2.0	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 50mA			2.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 3A; V <sub>CE</sub> = 3V			2.5	V
І <sub>сво</sub>	Collector Cutoff Current	V <sub>CB</sub> = 60V; I <sub>E</sub> = 0			0.2	- mA
		V <sub>CB</sub> = 40V; I <sub>E</sub> = 0; T <sub>C</sub> = 150°C			2.0	
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 30V; I <sub>B</sub> = 0			0.5	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			5	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 3V	750			

#### **NOTICE:**

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